

Page 4, line 7, please insert the word "a" between "includes" and "method".

Page 4, line 13, please delete the word --the-- between "The" and "step".

Page 6, line 22, please delete the word --an-- and insert the word "a" between "includes" and "deep".

NE Page 7, line 8, please delete the word --allow-- and insert the word "allows" between "wall" and "formation".

Page 8, line 15, please delete the label --304-- and insert the label "302" after "n-doped active device region".

### IN THE CLAIMS

As indicated below, please **AMEND** claims 1 and 5.

- C1  
Sub F11
1. (Twice amended) A semiconductor isolation structure comprising:
- a substrate, the substrate comprising a surface;
  - a first device and a second device formed within the substrate;
  - an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:
    - a deep region which extends into the substrate, the deep region comprising a deep region cross-sectional area;
    - a shallow region which extends to the surface of the substrate, the shallow region comprising:
      - a protective outer wall adjacent to the substrate;
      - an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall: and

the shallow region having a shallow region cross-sectional area;

wherein

the deep region cross-sectional area is greater than the shallow region

cross-sectional area.

5. (Twice amended) A semiconductor isolation structure comprising:

a substrate, the substrate comprising a surface;

a first device and a second device formed within the substrate;

an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:

a deep region which extends into the substrate, the deep region comprising an oxide;

a shallow region which extend to the surface of the substrate, the shallow region comprising:

a protective outer wall adjacent to the substrate,

an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall.

#### REMARKS

Claims 1, 2 and 4-6 are pending. Claim 3 has been previously canceled. The Specification has been amended to correct some egregious typographical errors. Claims 1 and 5 have also been amended. No new matter was added when making the amendments to the specification or claims.

#### ***Rejected Claims - 35 U.S.C. 112, first paragraph***

The Office Action stated that Claims 1, 2 and 4-6 stand rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in